COURSE CODE	COURSE NAME	L-T-P-C	YEAR OF INTRODUCTION
EC402	**NANOELECTRONICS**	**3-0-0 -3**	**2016**

Prerequisite: EC203 Solid State Devices, EC304 VLSI

Course objectives:

- To introduce the concepts of nanoelectronics.

Syllabus:

Introduction to nanotechnology, Mesoscopic physics, trends in microelectronics and optoelectronics, characteristic lengths in mesoscopic systems, Quantum mechanical coherence, Schrodinger's Equation, wave function, Low dimensional structures Quantum wells, Basic properties of two dimensional semiconductor nanostructures, Quantum wires and quantum dots, carbon nano tube, grapheme, Introduction to methods of fabrication of nano-layers, Introduction to characterization of nanostructures, Principle of operation of Scanning Tunnelling Microscope, X-Ray Diffraction analysis, MOSFET structures, Quantum wells, modulation doped quantum wells, multiple quantum wells, The concept of super lattices, Transport of charge in Nanostructures under Electric field, Transport of charge in magnetic field, Nanoelectonic devices, principle of NEMS

Expected outcome:

- The students will be able to understand basic concepts of nanoelectronic devices and nano technology.

Text Books:

1. J.M. Martinez-Duart, R.J. Martin Palma, F. Agulle Rueda Nanotechnology for Microelectronics and optoelectronics, Elsevier, 2006
2. W.R. Fahrner, Nanotechnology and Nanoelctronics, Springer, 2005

References:

1. Chattopadhyay, Banerjee, Introduction to Nanoscience & Technology, PHI, 2012
2. George W. Hanson, Fundamentals of Nanoelectronics, Pearson Education, 2009.
3. K. Goser, P. Glosekotter, J. Dienstuhl, Nanoelectronics and nanosystems, Springer 2004.
4. Murty, Shankar, Text book of Nanoscience and Nanotechnology, Universities Press, 2012.
5. Poole, Introduction to Nanotechnology, John Wiley, 2006.
6. Supriyo Dutta, Quantum Transport- Atom to transistor, Cambridge, 2013.

Course Plan

Module	Course contents	Hours	End Sem. Exam Marks
I	Introduction to nanotechnology, Impacts, Limitations of conventional microelectronics, Trends in microelectronics and optoelectronics	1	**15%**
	Mesoscopic physics, trends in microelectronics and optoelectronics, characteristic lengths in mesoscopic systems, Quantum mechanical coherence	2	
	Classification of Nano structures, Low dimensional structures Quantum wells, wires and dots, Density of states and dimensionality	1	

	Basic properties of two dimensional semiconductor nanostructures, square quantum wells of finite depth, parabolic and triangular quantum wells,	2	
	Quantum wires and quantum dots, carbon nano tube, graphene	1	
II	Introduction to methods of fabrication of nano-layers, different approaches, physical vapour deposition, chemical vapour deposition	2	**15%**
	Molecular Beam Epitaxy, Ion Implantation, Formation of Silicon Dioxide- dry and wet oxidation methods.	2	
	Fabrication of nano particle- grinding with iron balls, laser ablation, reduction methods, sol gel, self assembly, precipitation of quantum dots.	2	
FIRST INTERNAL EXAM			
III	Introduction to characterization of nanostructures, tools used for of nano materials characterization, microscope-optical, electron, and electron microscope.	2	**15%**
	Principle of operation of Scanning Tunnelling Microscope, Atomic Force Microscope, Scanning Electron microscope, Specimen interaction. Transmission Electron Microscope	2	
	X-Ray Diffraction analysis, PL & UV Spectroscopy, Particle size analyser.	2	
IV	Two dimensional electronic system, two dimensional behaviour, MOSFET structures, Heterojunctions	2	**15%**
	Quantum wells, modulation doped quantum wells, multiple quantum wells	2	
	The concept of super lattices Kronig - Penney model of super lattice.	2	
V	Transport of charge in Nanostructures under Electric field - parallel transport, hot electrons, perpendicular transport.	2	**20%**
	Quantum transport in nanostructures, Coulomb blockade	2	
	Transport of charge in magnetic field - Effect of magnetic field on a crystal. Aharonov-Bohm effect, the Shubnikov-de Hass effect, the quantum Hall effect.	3	
VI	Nanoelectonic devices- MODFETS, heterojunction bipolar transistors	1	**20%**
	Resonant tunnel effect, RTD, RTT, Hot electron transistors	2	
	Coulomb blockade effect and single electron transistor, CNT transistors	2	
	Heterostructure semiconductor laser	1	
	Quantum well laser, quantum dot LED, quantum dot laser	2	
	Quantum well optical modulator, quantum well sub band photo detectors, principle of NEMS.	2	
END SEMESTER EXAM			

Question Paper Pattern

The question paper shall consist of three parts. Part A covers modules I and II, Part B covers modules III and IV, and Part C covers modules V and VI. Each part has three questions uniformly covering the two modules and each question can have maximum four subdivisions. In each part, any two questions are to be answered. Mark patterns are as per the syllabus with 70% for theory and 30% for logical/numerical problems, derivation and proof.